

# HCO65S10D1

## eSiC Silicon Carbide Schottky Diode

650 V, 10 A

### Features

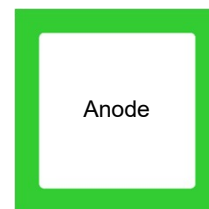
- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature

$V_{RRM}$	$I_F$	$T_{J,max}$	$Q_C$
650 V	10 A	175 °C	39 nC

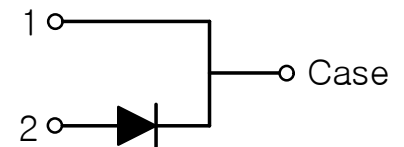
### Applications

- Power Factor Correction
- Industrial Power Supplies
- Solar Inverter, UPS

### Die Configuration



\*Cathode : Bottom



### Die Mechanical Parameters

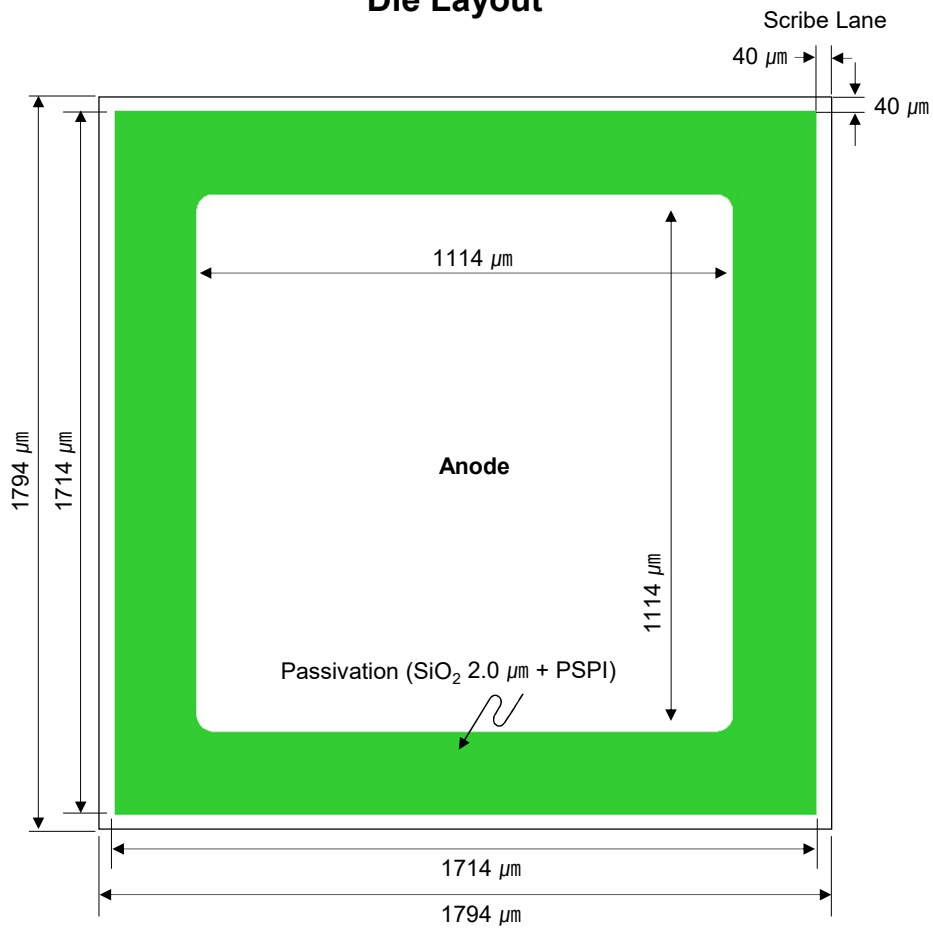
Parameter	Typical Value	Unit
Wafer Diameter	6	inch
Die Dimensions (W x L x T)	1794 x 1794 x 180	μm
Anode Metallization (AlCu)	4	μm
Bottom Cathode Metallization (Ti/Ni/Ag)	0.5	μm
Recommended Source Bond Wire	Al 8mils x 2	ea
Gross Die (Single chip of wafer)	4,936	ea

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ ) (Note1)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_F$	Forward Voltage	$I_F = 10 \text{ A}, T_C = 25^\circ\text{C}$		1.30	1.60	V
$I_R$	Reverse Current	$V_R = 650 \text{ V}, T_C = 25^\circ\text{C}$		-	100	μA

1. Based on TO220 package.

Die Layout



Wafer Sawing Information

